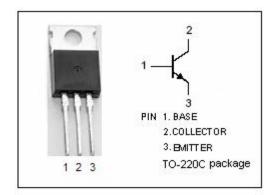


isc Silicon NPN Power Transistor

2SC4848

DESCRIPTION

- · Low Collector Saturation Voltage
 - : $V_{CE(sat)} = 0.6V(Max)@ I_C = 5A$
- · Collector-Emitter Breakdown Voltage-
 - : V_{(BR)CEO}= 120V (Min)
- · High Switching Speed
- Wide Area of Safe Operation
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

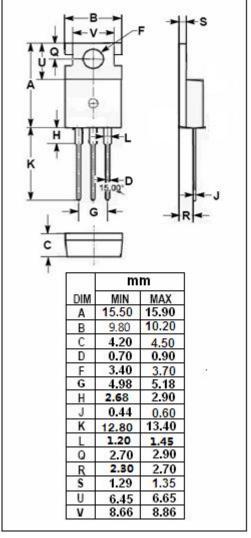


APPLICATIONS

 Designed for power amplifier and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{СВО}	Collector-Base Voltage	250	V	
V _{CEO}	Collector-Emitter Voltage	120	V	
V _{EBO}	Emitter-Base Voltage	12	V	
lc	Collector Current-Continuous	7	Α	
Ісм	Collector Current-Pulse 15		Α	
P _C	Collector Power Dissipation @ T _a =25°C	2	W	
	Collector Power Dissipation @ Tc=25°C	40		
TJ	Junction Temperature	150	$^{\circ}$	
T _{stg}	Storage Temperature Range -55~150		$^{\circ}$	





ISC Silicon NPN Power Transistor

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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

16-25 C unless otherwise specified									
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V _{CEX(SUS)}	Collector-Emitter Breakdown Voltage	I_{CP} = 8A; I_{B1} = $-I_{B2}$ = 0.5A, I_{C} = 5A; I_{C} = 200 μ H, clamped	125			V			
$V_{\text{CE}(\text{sat})}$	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 0.5A			0.6	V			
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I _C = 5A; I _B = 0.5A			1.2	V			
I _{CBO}	Collector Cutoff Current	V _{CB} = 100V; I _E = 0			10	μА			
Iceo	Collector Cutoff Current	V _{CE} = 100V; I _B = 0; T _a = 125℃			2.0	mA			
I _{EBO}	Emitter Cutoff Current	V _{EB} = 12V; I _C = 0			10	μА			
h _{FE}	DC Current Gain	I _C = 3A; V _{CE} = 5V	100		200				
f⊤	Current-Gain—Bandwidth Product	I _E = -0.5A; V _{CE} = 10V		20		MHz			
Сов	Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} = 1.0MHz		150		pF			
Switching times									
t _{on}	Turn-on Time				0.5	μS			
t _{stg}	Storage Time	I _C = 5A ;I _{B1} = -I _{B2} = 0.5A; R _L = 10 Ω ; V _{CC} ≈ 50V			2.5	μS			
t _f	Fall Time				0.5	μS			

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